

# Rapid Thermal Process Oven with Vacuum up to 150 mm dia. or 156 mm x 156 mm substrate size



- For wafer size up to 150 mm dia.
- Ramp up rate up to 150 K/sec
- Control **SIMATIC**® with 7" touch panel
- Vacuum up to 10<sup>-3</sup> hPa
- Process gas line with MFC for N<sub>2</sub>

Technical and design changes reserved

# FEATURE

- Precise fast ramp up and fast ramp down rates
- Excellent temperature uniformity
- Up to 4 gas lines (MFC)
- Integrated data logging
- Heated by Infrared Lamps
- 50 programs with 50 steps each
- Small foot print

# APPLICATION

- Implantation/Contact Annealing
- RTP, RTA, RTO, RTN
- Operation with inert gases, Oxygen, Hydrogen, Forming gas
- SiAu, SiAl, SiMo Alloying
- Low k dielectrica
- Crystallization & densification
- Si-Solar Wafer Cells on glass by Si-Wafer bonding

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- Rapid Thermal Annealing Process Oven with vacuum
- Touch Panel Svivel
- Programmable temperature profiles
- Record of process data
- Process in different gas atmospheres

#### APPLICATION

The **RTP-150**-EP Rapid Thermal Annealing Vacuum oven is an excellent tool for various semiconductor up to 150 mm diameterwafer or 156 mm x 156 mm s u b s t r a t e s i z e.

Some examples for applications: Laboratory furnace for all kind of developers implementing and researching new processes, prototype research, environmental research purposes and for small preseries or series.

#### PROCESS GASES

The RTP-150-EP can be used with standard process gases, like Nitrogen, Oxygen, Forming Gas. The chamber is sealed and can easily be cleaned.

#### **FLOW METER**

One gas line with Mass Flow Controller (MFC) for Nitrogen (5 nlm = norm liter per minute) is default, three more gas lines **(Option: MFC)** are possible.

#### VACUUM

The system is vacuum capable of up to 10<sup>3</sup> hPa. For higher vacuum we offer the model **RTP-150-EP-HV** (see separate data sheet)

#### HEATING

The maximal achievable temperature is 1000 °C. Key features are precisely controlled fast ramp-up 150 K/sec) and excellent ramp-down rates (depends on temperature and loading).

#### TEMPERATURE

The RTP-150-EP allows an excellent temperature distribution and homogenity. Optionally a graphite suzceptor can be inserted into the quartz chamber (**Option: GP Graphite Plate or Suszeptor**).

#### PROGRAMMING

The RTP-150-EP is equipped with a 7" touch panel which allows easy and comfortable programming directly on the unit.50 programs with 50 steps each can be stored. Unlimited programs can be up- and downloaded from external storage medium.



#### PROCESS CONTROL

The software allows the permanent monitoring, read- out and analysis of >temperature >process gas flow >cooling water level status >pressure value and status

#### COOLING

The cooling of the parts in the quartz chamber is realized by Nitrogen gas which will be led through the chamber. For chamber cooling we recommend a closed loop water cooling system.

(Accessories: WC-III or WC-IV)

#### **OTHERS**

An interlock function as well as an Emergency-OFF-Button (EMO) are default.

#### SPECIAL

This oven can also be orderd as "double chamber oven". By adding a second process chamber (Option: PC-150) the oven does have 2 process chambers and one controller unit. This saves money when 2 different processes are needed and the chambers shall not be cleaned due to contamination or other reasons.

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# SPECIFICATION

Max. part size	150 mm dia. or 156 mm x 156 mm
Chamber material	Quartz glass chamber
Part holder	Quartz universal holder for either 156 x 156 mm solar wafer
	or 150mm wafer diameter
Vacuum capability	Up to $10^{-3}$ hPa (optionally up to $10^{-6}$ hPA)
Process chamber size	325 mm x 214 mm x 40 mm (W x D x H)
Temperature max.	1000 °C (higher on request)
Temp. uniformity	≤ 1,5% of set temperature
Heating	Top and bottom heating with 24 IR Lamps (2x21 kW)
Ramp up rate	Up to 150 K/sec
Ramp down rate	T= 1000°C > 400°C: 200 K/min, T= 400°C > 100°C: 30 K/min
Flow Controller	Mass Flow Controller (Nitrogen 5 nlm = norm liter per minute)
Controller	SIMACTIC <sup>®</sup> 50 programs with 50 steps each
Chamber cooling	Water cooled
Substrate Cooling	By Nitrogen Gas

# TECHNICAL DATA

Dimension oven Weight Electrical Connection 503 mm x 525 mm x 570 mm (W x D x H) 55 kg 2 x (400/230V, 21kW)

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## OPTIONS

RTP-H2 RTP-H2S RTP-MFC	Hydrogen option with Safety device (Sensor and Hydrogen monitoring) Safety device for Hydrogen option (with cover and sensor) Additional process gas line with Mass Flow Controller (max. 3 add) * * = all in all max. 4 process gas lines
RTP-Ox	Oxygen Analyser to measure Oxygen residues (not in combination with Hydrogen Option)
RTP-MM	Moisture Analyzer to measure moisture residues in the chamber
RTP-SW	Switchbox for chiller and vacuum pump
RTP-TC	add. Thermocouple to measure on device (plugged in chamber, max. 1)
<b>RTP-VAC I</b>	Basic Vacuum up to 3 hPa, Vacuum sensor, vacuum valve excl. pump
RTP-VAC I	Comfort Vacuum up to 10 <sup>-3</sup> hPa, Pirani Sensor, vacuum valve, excl.pump
RTP-VCR	Tubing made of VCR (welded)
RTP-CAB	Oven integrated as floor model into a cabinet with Uni. Heat Exchanger

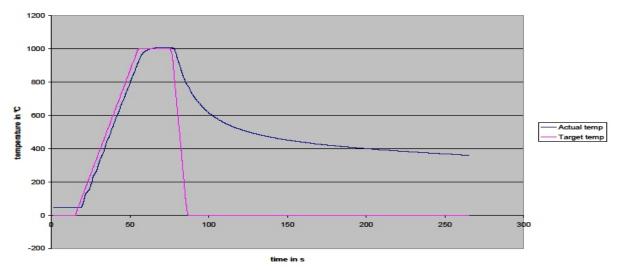
## ACCESSORIES

**RTP-GP-150** Graphite Plate or susceptor (optional SiC coated)

**RTP-PC-150** add. 100 mm oven chamber ("double chamber( for usage of 2 chambers) **RTP-QR-75** Adapter (quartz ring) for 75 mm wafer

RTP-QR-100 Adapter (quartz ring) for 100 mm wafer

MP RVP Membrane/diaphragm pump for vacuum up to 3 hPa Rotary vane pump or dry pump for vacuum up to 10<sup>-3</sup> hPa



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